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TECHNOLOGY CENTER 2800

Fax

To: Assistant Commissioner for Patents

From: David Bonham
(703) 433-0510

Fax: 703-872-9319

Total pages: 11

Phone:

Date: 4/10/03

Re: In connection with prosecution in Serial. No.
09/881,254, please find enclosed an Amendment
and Response to the final Office Action mailed
February 13, 2003.

CC:

Sincerely,

David Bonham

☐ **Urgent** ☐ **For Review** ☐ **Please Comment** ☐ **Please Reply** ☐ **Please Recycle**

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Please do Not enter. *[Signature]*
Serial No. 09/881,254

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#10/B
Andt
N/E
J. McMillan
4/16/03

Applicant: Fwu-Iuan Hshieh et al.
Serial No.: 09/881,254
Filed: 06/14/2001
Title: SYMMETRIC TRENCH MOSFET DEVICE AND METHOD OF MAKING SAME
Art Unit: 2826
Examiner: Mondt, Johannees P.
Docket No.: GS 134
VIA FACSIMILE 703-872-9319
Box AF
Assistant Commissioner for Patents
Washington, D.C. 20231

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AMENDMENT AND RESPONSE

Sir:

Responsive to the outstanding Office Action dated February 13, 2003 in the above-identified patent application, please enter the following amendments and remarks:

IN THE CLAIMS:

Please amend claims 1 and 14 as follows:

1. (Amended) A trench MOSFET transistor device comprising:
- a drain region of a first conductivity type;
 - a body region of a second conductivity type provided over said drain region, said drain region and said body region forming a first junction;
 - a source region of said first conductivity type provided over said body region, said source region and said body region forming a second junction;
 - source metal disposed on an upper surface of said source region;

PLEASE ENTER (IN VIEW OF ACE)
Thanks. *[Signature]* (5/31/03)

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